

www.vishay.com Vishay Semiconductors

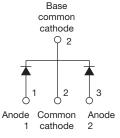
## Ultrafast Rectifier, 2 x 5 A FRED Pt®

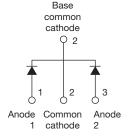




TO-263AB (D<sup>2</sup>PAK)

**TO-262AA** 





VS-MURB1020CTPbF

VS-MURB1020CT-1PbF

PRODUCT SUMMAR	RY
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA
I <sub>F(AV)</sub>	2 x 5 A
V <sub>R</sub>	200 V
V <sub>F</sub> at I <sub>F</sub>	0.87 V
t <sub>rr</sub>	25 ns
T <sub>J</sub> max.	175 °C
Diode variation	Common cathode

#### **FEATURES**

- Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C









## **HALOGEN** FREE

#### **DESCRIPTION / APPLICATIONS**

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V		
Average rectified forward current	per leg			5	5		
Average rectified forward current	total device	I <sub>F(AV)</sub>	Rated V <sub>R</sub> , T <sub>C</sub> = 149 °C	10	Α		
Non-repetitive peak surge current per leg		I <sub>FSM</sub>		50	A		
Peak repetitive forward current per	leg	I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 149 °C	10			
Operating junction and storage tem	peratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS				MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	200	-	-		
Forward voltage		I <sub>F</sub> = 5 A, T <sub>J</sub> = 25 °C	-	0.99	1.08	V	
	V <sub>F</sub>	I <sub>F</sub> = 5 A, T <sub>J</sub> = 125 °C	-	0.87	0.99	]	
Forward voltage		I <sub>F</sub> = 10 A, T <sub>J</sub> = 25 °C	-	1.12	1.25		
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	1.02	1.20		
Deverage leakage assurent		$V_R = V_R$ rated	-	-	10		
Reverse leakage current	I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	-	250	μA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	8	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ	



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt = 5	0 A/μs, V <sub>R</sub> = 30 V	-	-	35	
Dovoroo rooovery time		I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0 A, I <sub>REC</sub> = 0.25 V		-	-	25	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 200 \text{ A/µs}$ $V_R = 160 \text{ V}$	-	24	-	ns
		T <sub>J</sub> = 125 °C		-	35	-	
Peak recovery current		T <sub>J</sub> = 25 °C		-	3.3	-	А
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	5.0	-	] ^
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	33	-	nC
	$Q_{rr}$	T <sub>J</sub> = 125 °C		-	76	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	5		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	50	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Waight			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
		Case style TO-263AB (D2PAK)	MURB1020CT				
Marking device		Case style TO-262	MURB1020CT-1				

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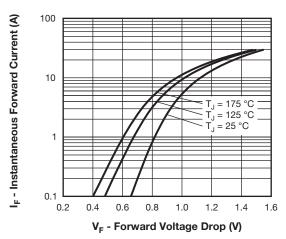


Fig. 1 - Typical Forward Voltage Drop Characteristics

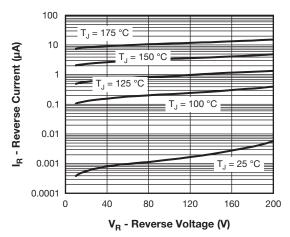


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

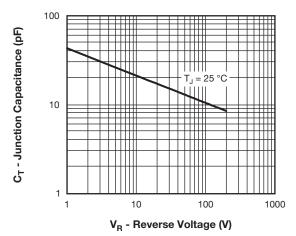


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

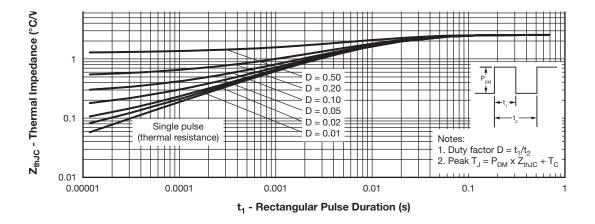


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

V<sub>R</sub> = 160 V T<sub>1</sub> = 125 °C

 $T_J = 25 \, ^{\circ}C$ 

50

30

20

10

100

t<sub>rr</sub> (ns)

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### Vishay Semiconductors

1000

1000

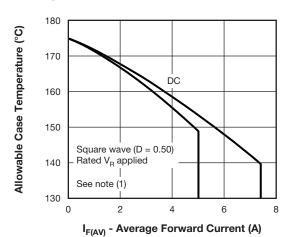


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

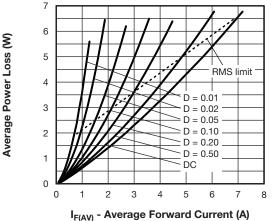
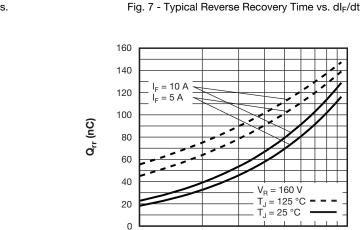


Fig. 6 - Forward Power Loss Characteristics



100

 $dI_F/dt$  (A/ $\mu$ s) Fig. 8 - Typical Stored Charge vs.  $dI_F/dt$ 

dl<sub>F</sub>/dt (A/µs)

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 

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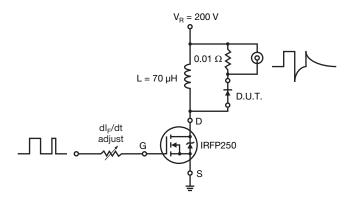
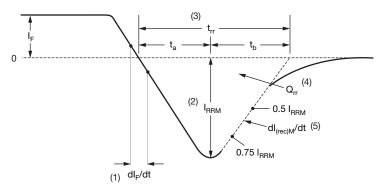


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

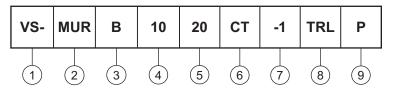
(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

#### Device code



Vishay Semiconductors product

Ultrafast MUR series

3 4 5 6  $B = D^2PAK/TO-262$ 

Current rating (10 = 10 A)

Voltage rating (20 = 200 V)

CT = center tap (dual)

• None = D<sup>2</sup>PAK

• -1 = TO-262

8 • None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D<sup>2</sup>PAK package)

• TRR = tape and reel (right oriented, for D<sup>2</sup>PAK package)

9 • PbF = lead (Pb)-free (for TO-262 and D<sup>2</sup>PAK tube)

• P = lead (Pb)-free (for D<sup>2</sup>PAK TRR and TRL)

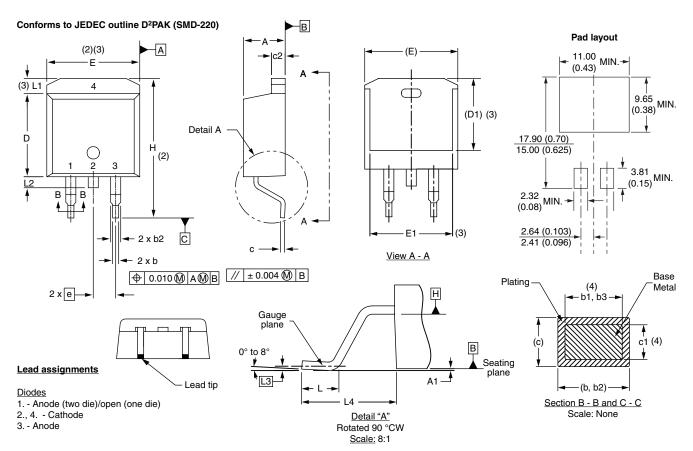
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95014</u>					
Part marking information	www.vishay.com/doc?95008				
Packaging information	www.vishay.com/doc?95032				



### Vishay High Power Products

# **D<sup>2</sup>PAK**, **TO-262**

#### **DIMENSIONS FOR D<sup>2</sup>PAK** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTEC
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$  Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

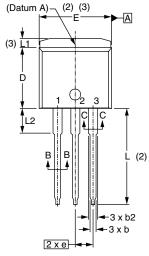
Vishay High Power Products

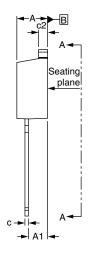
D<sup>2</sup>PAK, TO-262

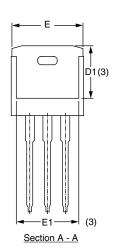


#### **DIMENSIONS FOR TO-262** in millimeters and inches

# Modified JEDEC outline TO-262 (Datum A) (2) (3)







**⊕** 0.010**⋒**|A**⋒**|B

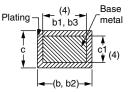
#### Lead assignments



#### **Diodes**

1. - Anode (two die)/open (one die) 2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100	) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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